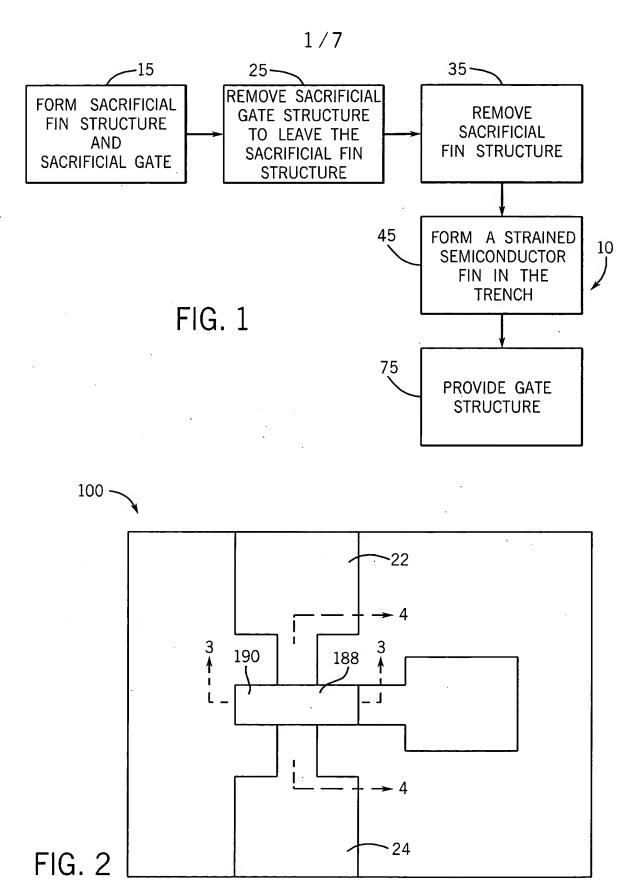
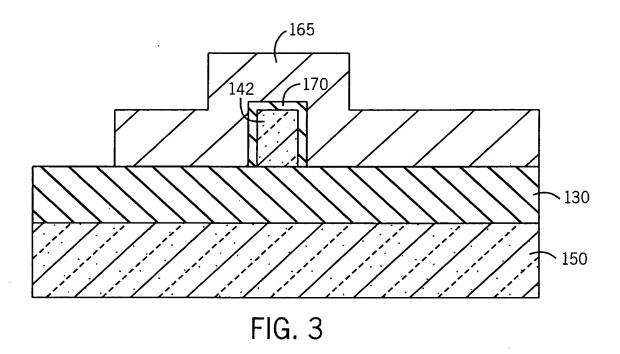
Title: A REPLACEMENT GATE STRAINED SILICON FINFET PROCESS

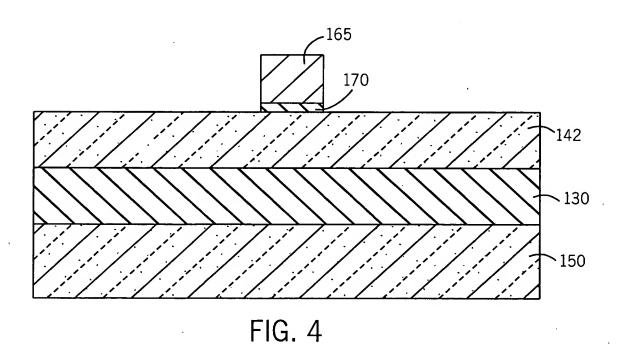
Inventor(s): Goo et al. DOCKET NO.: 039153-0680



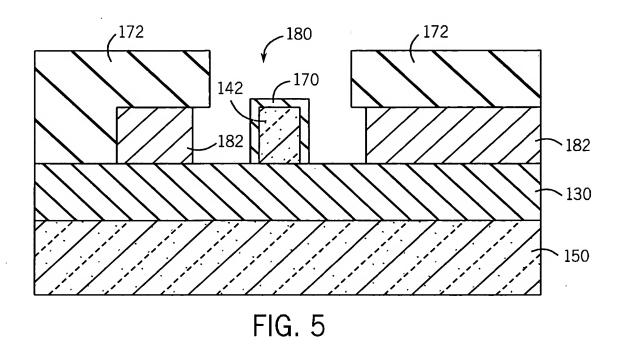
Inventor(s): Goo et al. DOCKET NO.: 039153-0680

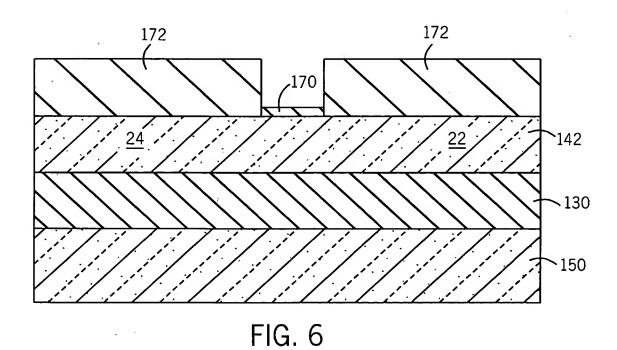
2 / 7





3 / 7

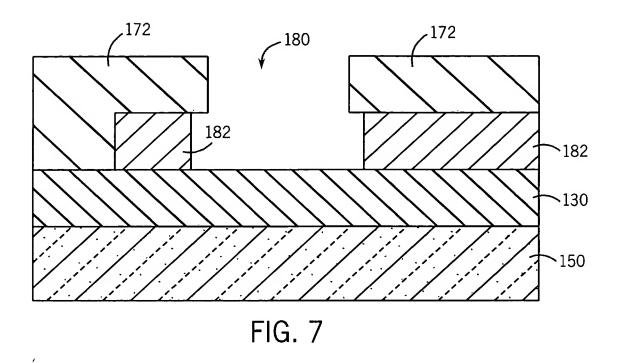


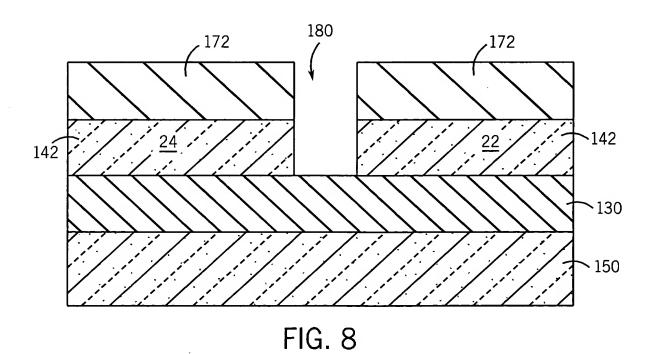


Title: A REPLACEMENT GATE STRAINED SILICON FINFET PROCESS

Inventor(s): Goo et al. DOCKET NO.: 039153-0680

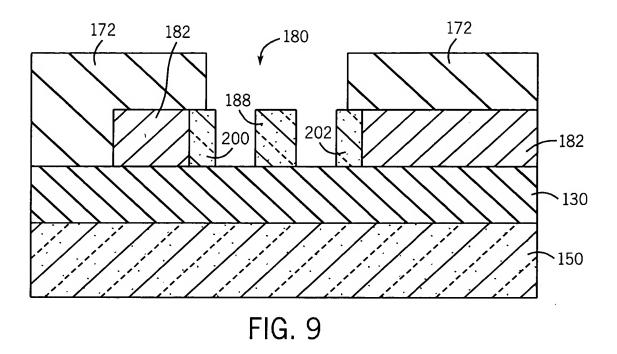
4 / 7

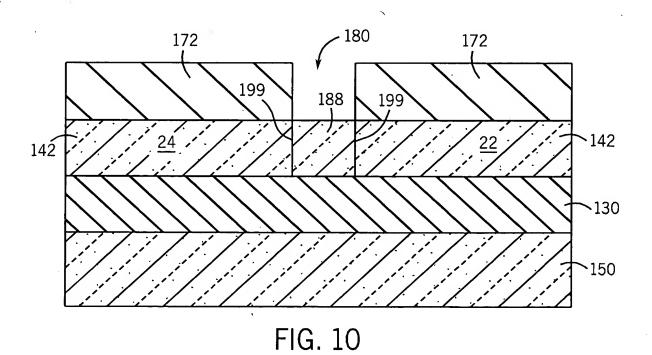




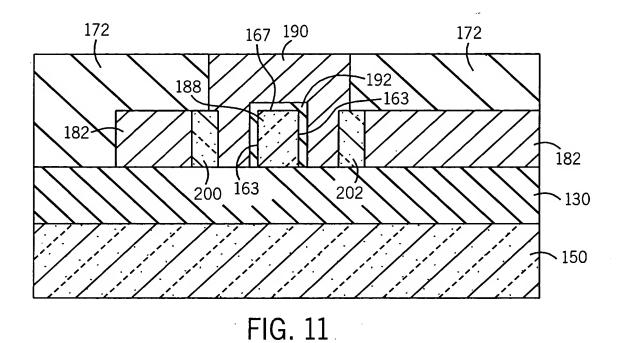
Inventor(s): Goo et al. DOCKET NO.: 039153-0680

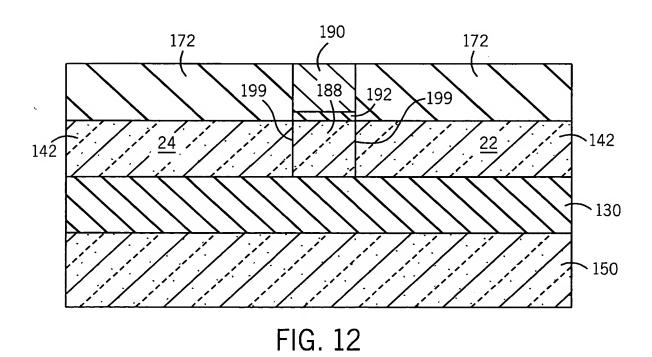
5 / 7











Inventor(s): Goo et al. DOCKET NO.: 039153-0680

7 / 7

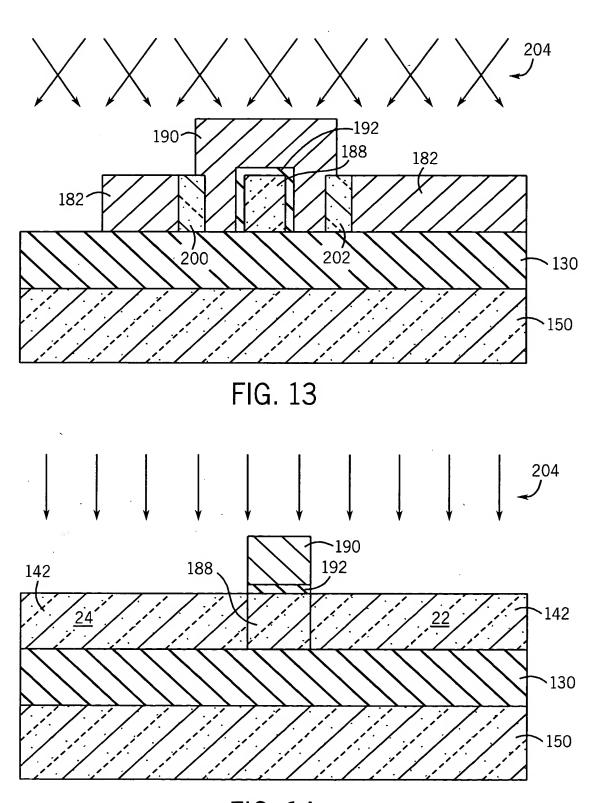


FIG. 14